

/ Descriptions

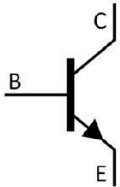
TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

High P_C , low $V_{CE(sat)}$, high current switching.

/ Applications

Medium power switching and muting, linear regulators, LCD back-lighting, supply line switching circuits.

/ Equivalent Circuit**/ Pinning**

PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

See Marking Instructions.

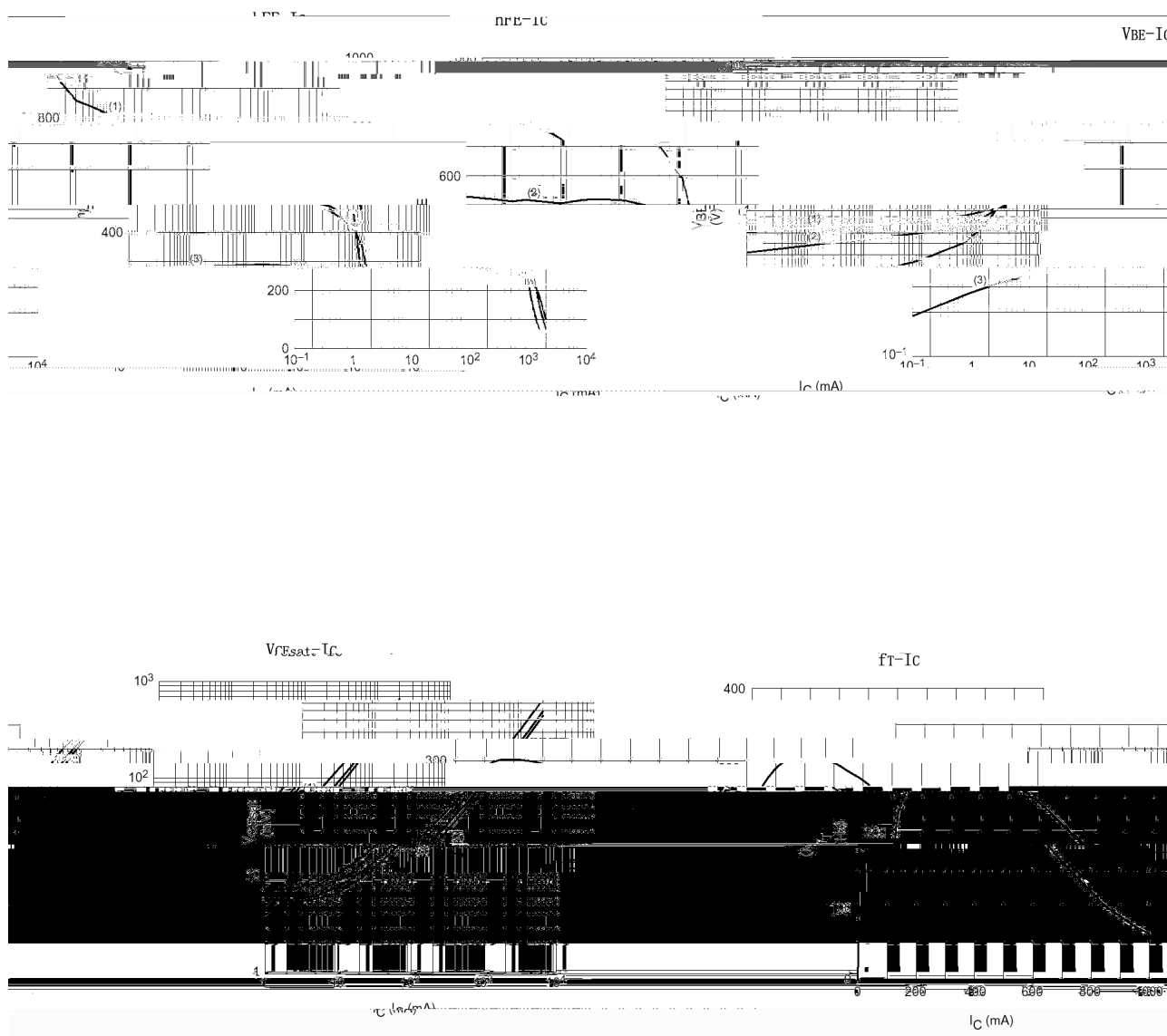
/ Absolute Maximum Ratings($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Peak Collector Current	I_{CM}	2.0	A
Peak Base Current	I_{BM}	1.0	A
Collector Power Dissipation	P_C	830	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics($T_a=25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=40V$ $I_E=0$			0.1	μA
Collector Cut-Off Current	I_{CEO}	$V_{CE}=30V$ $I_B=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5.0V$ $I_C=500mA$	300		900	
	$h_{FE(2)}$	$V_{CE}=5.0V$ $I_C=1.0mA$	300			
	$h_{FE(3)}$	$V_{CE}=5.0V$ $I_C=1.0A$	200			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=100mA$ $I_B=1.0mA$			200	mV
	$V_{CE(sat)(2)}$	$I_C=500mA$ $I_B=50mA$			250	mV
	$V_{CE(sat)(3)}$	$I_C=1.0A$ $I_B=100mA$			500	mV
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1.0A$ $I_B=100mA$			1.2	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=1.0A$			1.1	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=50mA$ $f=100MHz$	150			MHz
Collector Capacitance	C_C	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$			10	pF

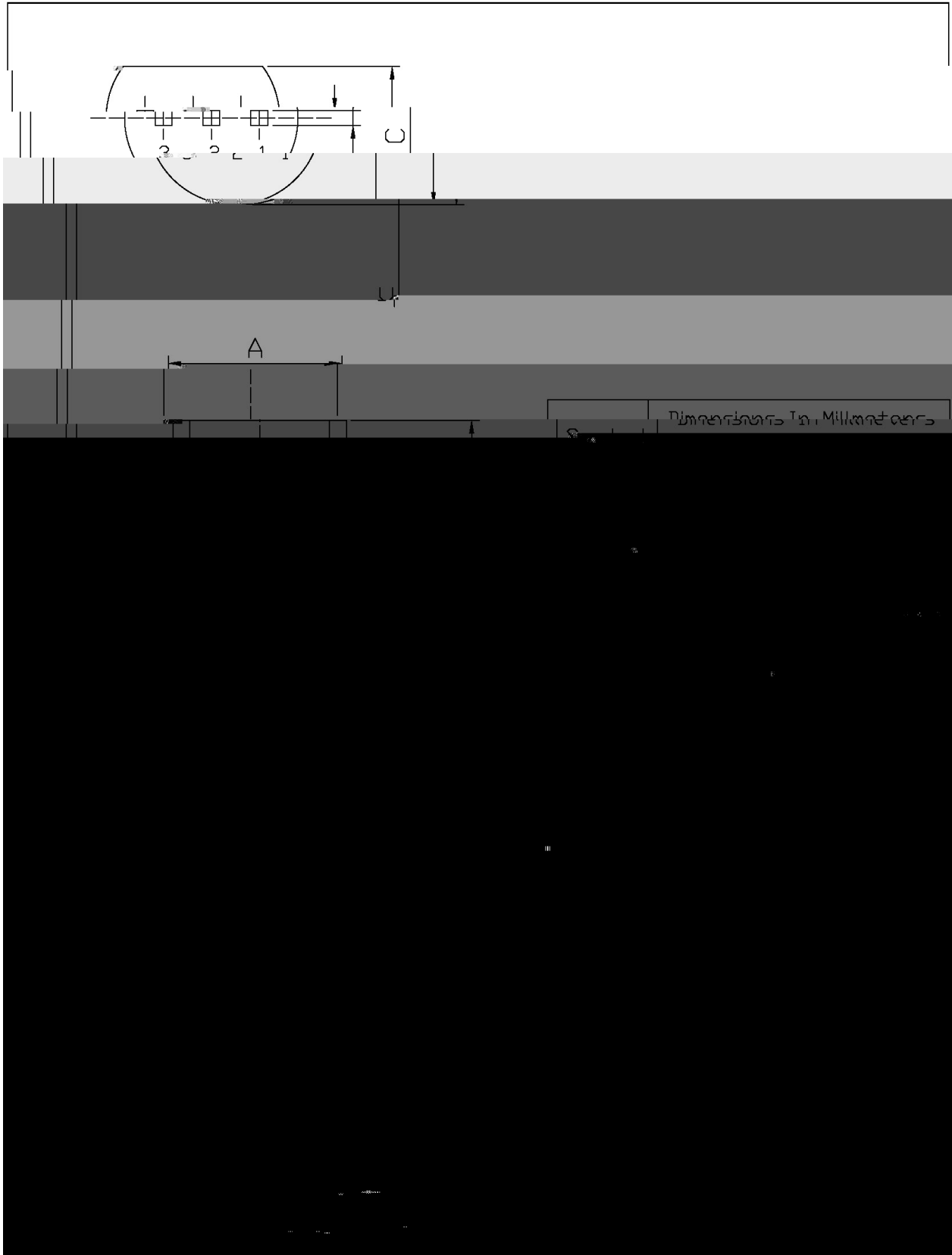
/ Electrical Characteristic Curve



/ Package Dimensions

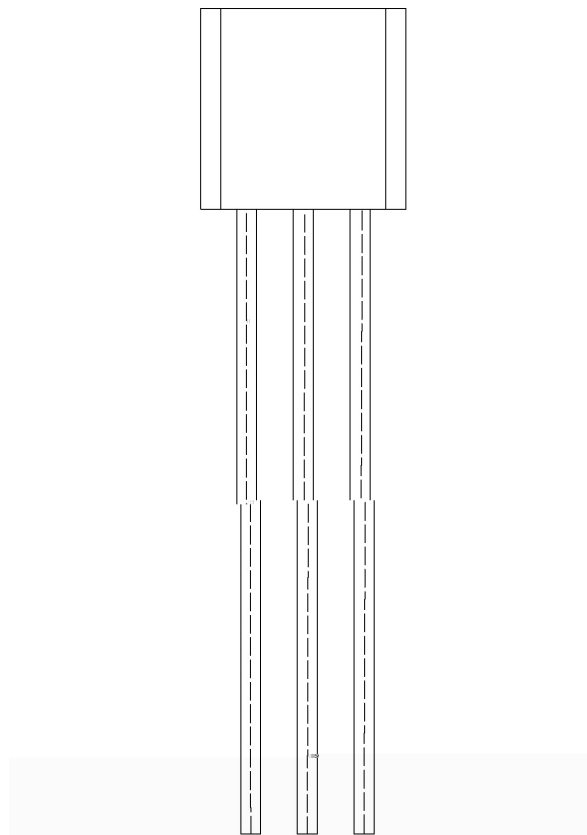
T0-92

Unit: mm





/ Marking Instructions

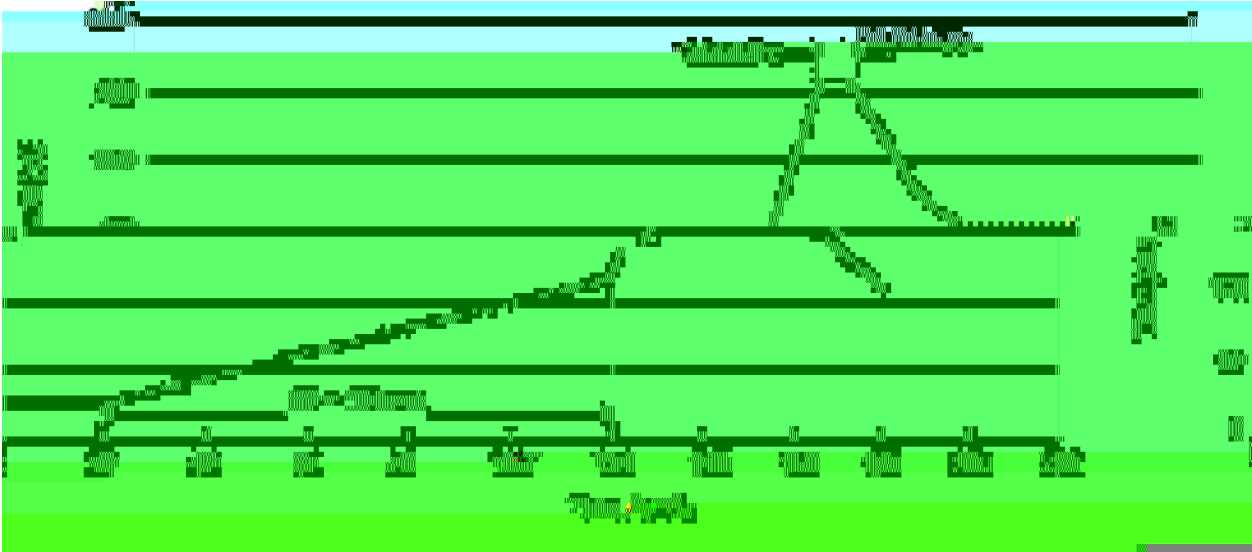


BR:

4140S

-566.7()-7371.1()-7371.1Lot No. Cod.,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp:270±5	Time:10±1 sec
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/ Packaging SPEC.

/ BULK

dBW(37#)